

# Designing, Building and Pitfalls of simple Class-E transmitters

A beginner's guide by a beginner experimenter

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# Overview

- Introduction to Class-E
- Design and implementation of a Class-E amplifier
- Selecting a FET
- Other component selection
- Good and not so good waveforms
- Special topics
- Ideas

# Introduction to Class-E

- Class A ( $360^\circ$ ), B( $180^\circ$ ) and C( $120^\circ$ )
- Class D: Switching amplifier
- Class E: Read the Sokal article!
  - General concept is high voltage and high current do not exist at the same time across the switching device (FET)
  - High efficiency (typically much better than 80%)
  - Easy to design, works every time!
  - Suitable for single FET transmitters

# Examples of Class-E transmitters

Table 2—Example Class-E Power Amplifiers

<i>Frequency</i>	<i>Power</i>	<i>Transistor</i>	<i>Collector or Drain Efficiency/PAE</i>	<i>Organization</i>	<i>Approximate Year</i>	<i>See Reference</i>
0.52-1.7 MHz	44 kW PEP	push-pull MOSFETs	95%	Broadcast Electronics, Inc	1992	34
14 MHz	110 W	International Rectifier IRF540	92%	Design Automation, Inc	1986	36
13.56 MHz, 27.12 MHz	2 kW	MOSFET	90%	Dressler Hochfrequenztechnik	1993	
13.56 MHz	3 kW, 5.5 kW	MOSFET	?%	Advanced Energy Industries, Inc	1992-1997	
27.12 MHz	22 W	International Rectifier IRF510	89-92%	Design Automation, Inc	1991	37
145 MHz	2.58 W	Siliconix VMP4 VMOSFET	96.5%/81.3%*	École Polytech. Féd. Lausanne	1980	32
300 MHz	30 W	push-pull BJTs	89%	Harris RF Communications	1992	39
450 MHz	14.96 W	combine 4 modules MRF873 BJT	89.5%	City Univ. of Hong Kong	1997	30
500 MHz	0.55 W	Siemens CLY5 GaAs MESFET	83%/80%	Univ. of Colorado	1995	23
840 MHz	1.24 W	GaAs MESFET	79%/77%	S. C. Cripps	<1999	40
850 MHz	1.6 W	GaAs MMIC	62.3% PAE	M/A-COM	1994	26
1 GHz	0.94 W	Siemens CLY5 GaAs MESFET	75%/73%	Univ. of Colorado	1995	22, 21
2.45 GHz	1.27 W	Fujitsu FLC30 GaAs MESFET	72% PAE	RCA David Sarnoff Res. Ctr.	1981	13
2.45 GHz†	210 mW	Raytheon RPC3315 MESFET	77%/68%/71%*	Design Automation, Inc	1979	33
5 GHz	0.61 W	Fujitsu FLK052WG MESFET	81%/72%	Univ. of Colorado	1996	12, 23
8.35 GHz	1.41 W	Fujitsu FLK202MH-14 MESFET	64%/48%	Univ. of Colorado	1999	41
10 GHz	100 mW	Alpha Ind. AFM04P2 MESFET	74%/62%	Univ. of Colorado	1999	42

\*Overall efficiency =  $P_{out}/(P_{dc} + P_{drive})$

†1/20 scaled-frequency model at 122.5 MHz; see Reference 33.

# Requirements

- A plan with a clear target ( $P_{out}$ ,  $V_{cc}$ , etc)
- Driving circuit (depends)
- A FET (common: Jaycar/eBay/RS/etc)
- Suitable Capacitors (eBay/Junkbox/Jaycar?)
- Suitable inductors (eBay/RS/Junkbox/etc)
- Fingers!
  - For testing which component gets hot!
- Oscilloscope and DMM
  - Waveforms help with troubleshooting
- Dummy load

# *Class-E RF Power Amplifiers*

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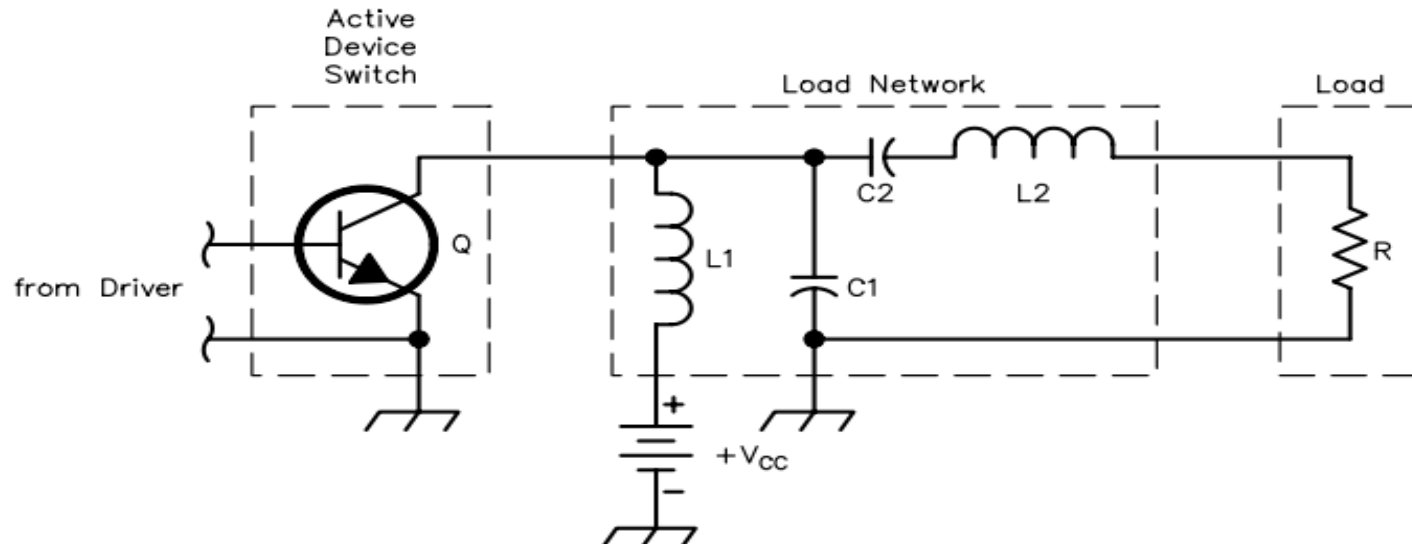
*Come learn about this highly efficient and widespread class of amplifiers. Here are principles of operation, improved design equations, optimization principles and experimental results.*

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By Nathan O. Sokal, WA1HQC  
of Design Automation, Inc  
ARRL Technical Advisor



# Sokal article (the important bits)



$$R = \left( \frac{(V_{CC} - V_o)^2}{P} \right) 0.576801 \left( 1.0000086 - \frac{0.414395}{Q_L} - \frac{0.577501}{Q_L^2} + \frac{0.205967}{Q_L^3} \right)$$

$$C1 = \frac{1}{34.2219 f R} \left( 0.99866 + \frac{0.91424}{Q_L} - \frac{1.03175}{Q_L^2} \right) + \frac{0.6}{(2\pi f)^2 L1}$$

$$C2 = \frac{1}{2\pi f R} \left( \frac{1}{Q_L - 0.104823} \right) \left( 1.00121 + \frac{1.01468}{Q_L - 1.7879} \right) - \frac{0.2}{(2\pi f)^2 L1}$$

$$L2 = \frac{Q_L R}{2\pi f}$$

# Design

- Sokal article
- VK2ZAY online calculator
- Alan Melia G3NYK spreadsheet
  - <http://www.alan.melia.btinternet.co.uk/classepa.htm>
- Driving circuit
  - Square wave, ~50% duty cycle, drive FET to saturation (8 or 9 volts, depends on FET)
  - MOSFET drivers
  - CMOS – TTL -DDS – Signal generator
  - The capacitive reactance of  $C_{iss}$  will determine the driving requirements



# Driving the FET

- Ferrite bead on gate pin or a few ohms in series to avoid parasitic VHF oscillations
- Driving a capacitor ( $C_{iss}$ )
- $X_c = 1/2 * \pi * f * C$
- For low C, F drive directly from CMOS IC?
- Dedicated MOSFET driver ICs
  - TC4420, TC4427, etc
- A FET to drive the FET?

# Design: common FETs

FET	$V_{ds}(I)$	$R_{ds(on)}$	$C_{iss}$	$C_{oss}$	Comments
2N7000	60 V (0.2A)	1.2 $\Omega$	20 pF	11 pF	QRP, maybe up to 1 W
IRF510	100 V (5.6A)	0.54 $\Omega$	135 pF	80 pF	Common 5 W to 10 W QRP FET
IRF520	100 V (9.2A)	0.27 $\Omega$	360 pF	150 pF	Around 20 W max?
IRF540	100 V (28A)	0.077 $\Omega$	1.7 nF	560 pF	100 W from 12 V?
IRF640	200 V (18A)	0.18 $\Omega$	1.3 nF	430 pF	200 W from 24 V?
IRF840	500 V (8A)	0.85 $\Omega$	1.2 nF	200 pF	For high voltage (100 V?) designs

Always check the correct datasheet for your component!

# Design: calculations

## Class-E RF Amplifier

Based on the Nathan Sokal WA1HQC equations.

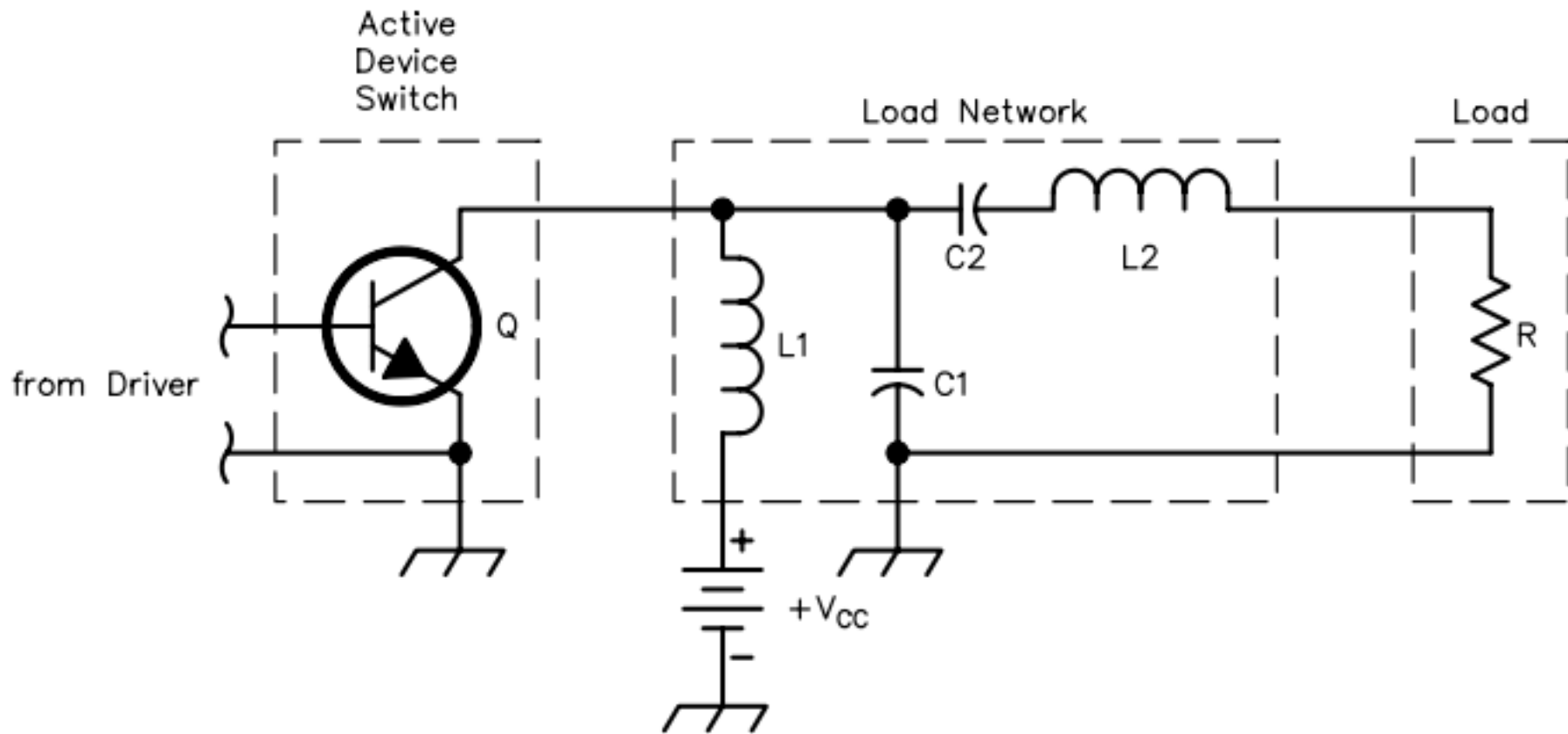
Power Output	<input type="text" value="25"/>	Watts
Supply Voltage	<input type="text" value="12.5"/>	Volts
Saturation Voltage	<input type="text" value="0.2"/>	Volts
Loaded Q	<input type="text" value="5"/>	1.79-∞
Frequency	<input type="text" value="137777"/>	Hertz
Feed Choke	<input type="text" value="0.00047"/>	Henries

calculate

<b>Load Resistance</b>	3.126 Ω
<b>C1</b>	79.055 nF
<b>C2</b>	98.846 nF
<b>L2</b>	18.058 uH

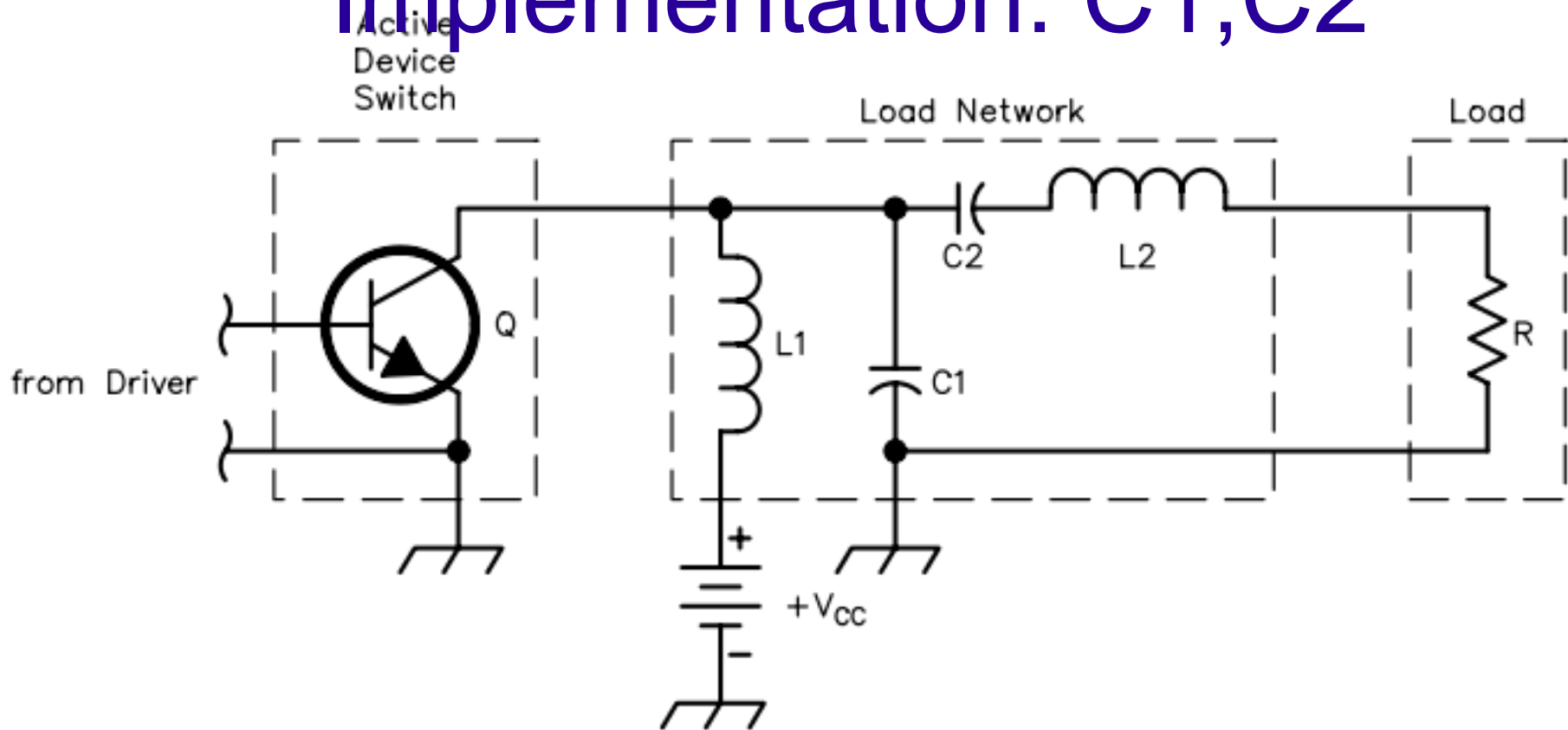
- VK2ZAY online Class-E calculator
  - **Experiment with it!**
- Feed Choke = L1
- Saturation Voltage is  $I^* R_{ds(on)}$
- 5 is a good starting value for Loaded Q
- Supply voltage should not be more than  $(V_{ds}/3.56)*SF$ 
  - SF: safety factor, 0.8 or 0.9 or so...

# Implementation: L1



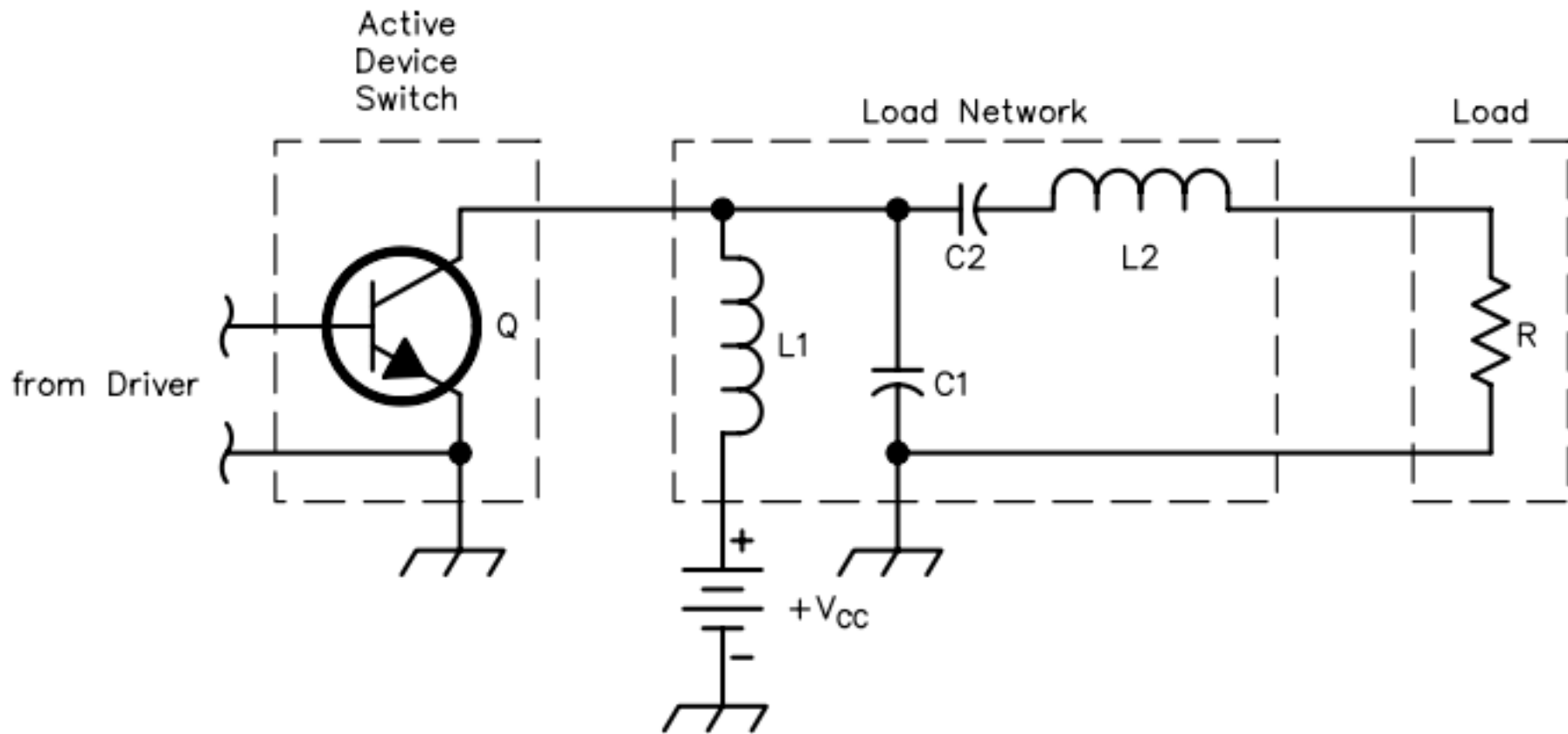
- Not critical!
- 30x the load impedance
- Ferrite toroid

# Implementation: C1,C2



- $C1 = C_{oss} + \text{Extra capacitance}$
- High current capacitors, WIMA FKP/MKP or Silvermica
- HV ceramic may be OK but beware of losses and temperature coefficient

# Implementation: L2



- Amidon mix 2 for LF to 40m, mix 6 for higher frequencies
- Critical

# Implementation: impedance transformer

- Primary: 3x or more the load impedance
  - $X_L = 2 * \pi * f * L$
- Secondary according to formula:
  - $N1/N2 = \text{SQRT}(Z1/Z2)$
- Ferrite
  - High AL RFI ferrites seem to work OK
  - Experiment
- Finger test for efficiency!



# Waveforms

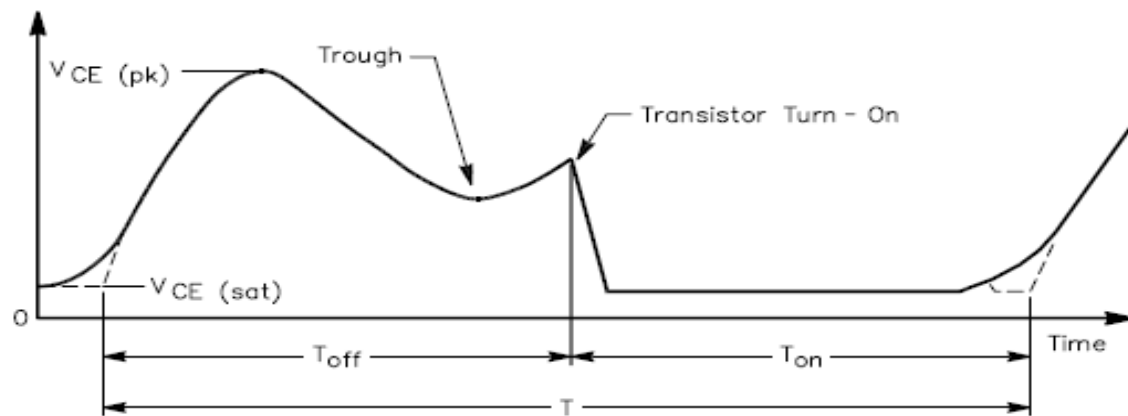


Fig 4—Typical mistuned  $V_{CE}$  waveform, showing transistor turn-on, turn-off and waveform "trough."

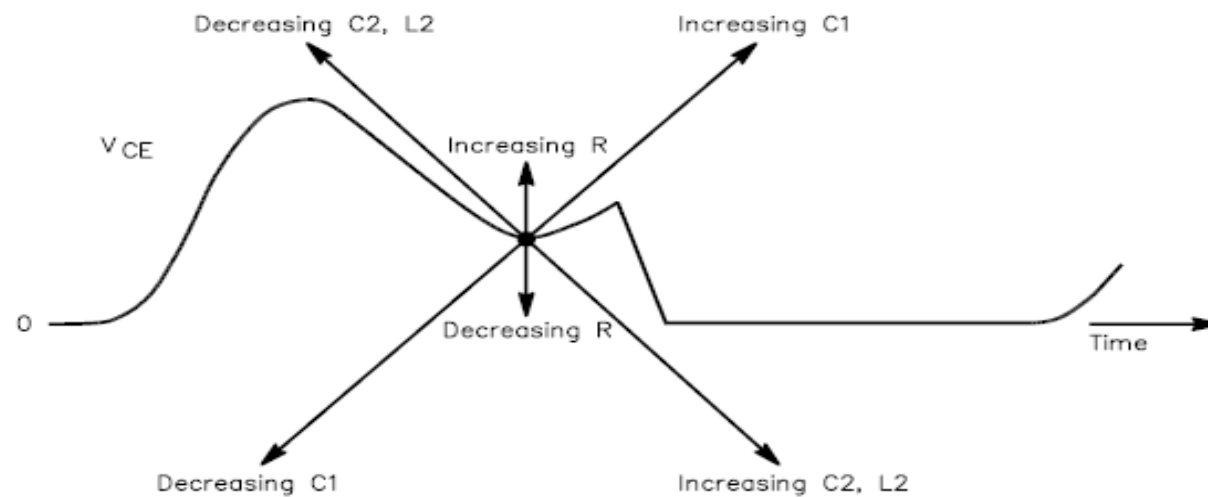
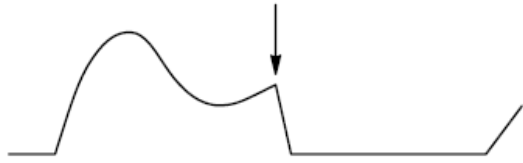
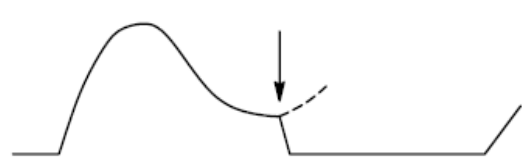
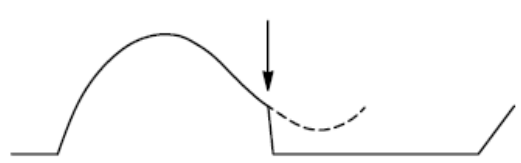
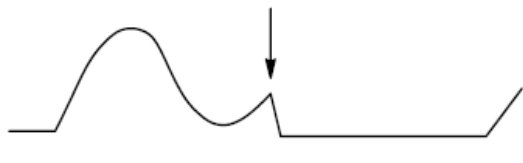
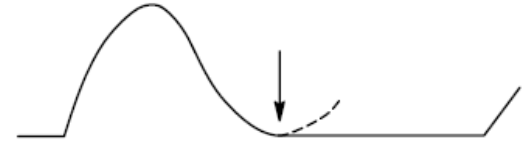

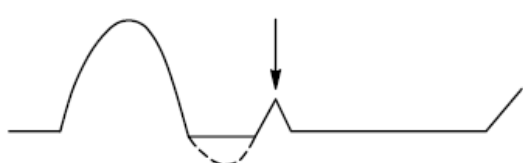
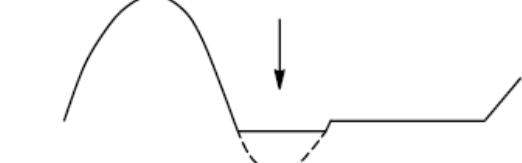
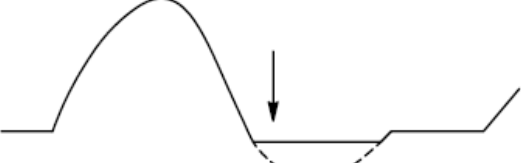


Fig 5—Effects of adjusting load-network components.

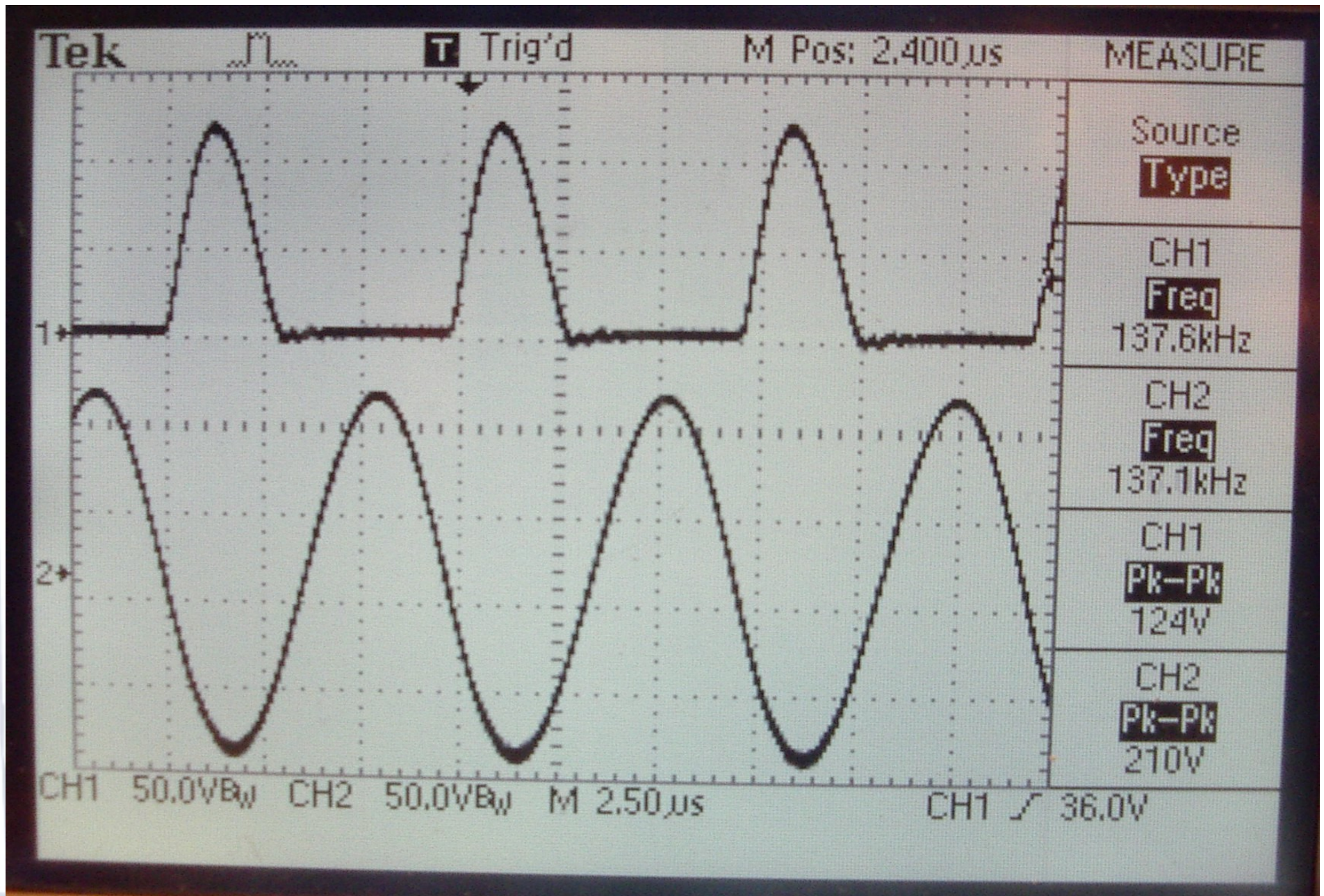
# More waveforms

$V_{CE}$  Slope at Transistor Turn On

$V_{CE}$ Relative to $V_{CE(sat)}$ at Time of Zero Slope	Positive; Increase (C1 Series C2)	Zero; Keep Same (C1 Series C2)	Negative; Decrease (C1 Series C2)
More Positive; Decrease C1/C2	 <p data-bbox="521 724 627 746">Increase C2</p>	 <p data-bbox="1021 724 1293 746">Decrease C1 and Increase C2</p>	 <p data-bbox="1687 724 1793 746">Decrease C1</p>
Equal; Keep Same C1/C2	 <p data-bbox="393 1069 759 1091">Increase C1 and C2 in same Proportion</p>	 <p data-bbox="953 1069 1361 1091">Finished Adjusting C1 and C2. Go to Step 7</p>	 <p data-bbox="1559 1069 1925 1091">Decrease C1 and C2 in Same Proportion</p>
More Negative; Increase C1/C2	 <p data-bbox="521 1412 627 1434">Increase C1</p>	 <p data-bbox="1021 1412 1293 1434">Increase C1 and Decrease C2</p>	 <p data-bbox="1687 1412 1793 1434">Decrease C2</p>



# Result: waveforms



# Finishing touch, hints and tips

- Harmonics are -20 dBc or better
- An LPF is needed (but it's not going to work very hard!)
  - WA4DSY web site
  - SM caps and -2 or -6 mix
- Heat sink on FET
- Toroid calculator
  - <http://toroid.info/T50-2>

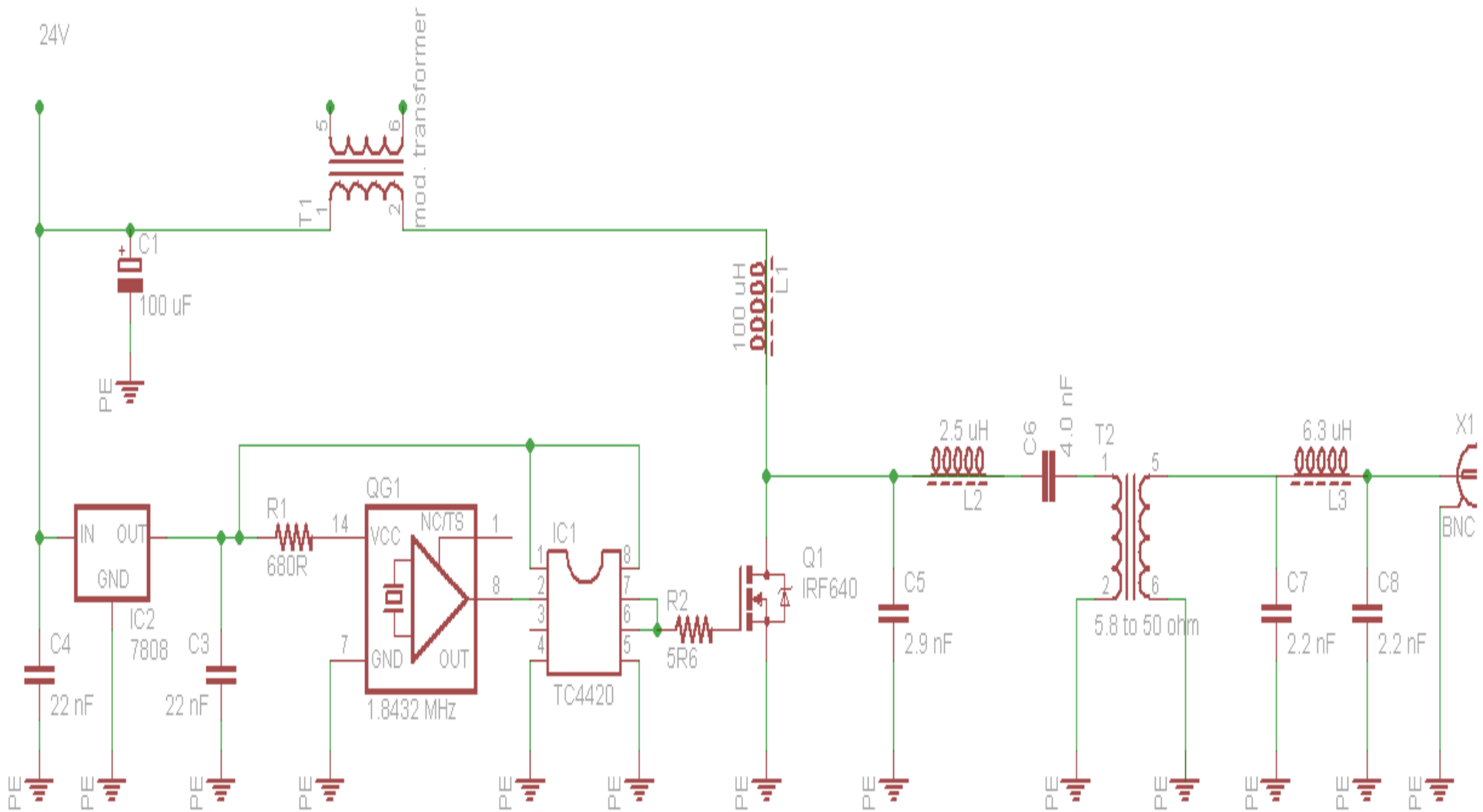


# Special topics: Amplitude modulation

- Easiest option: drain modulation
  - Voltage should swing between 0 V and  $2x V_{cc}$  for 100% modulation
  - Design for  $2x V_{cc}$ , ensure FET and other components are suitable for that power
  - Modulation transformer: dare I suggest a big power toroid with appropriate turns ratio?
- Other maybe interesting option: modulation by duty cycle change of the gate driving signal
  - Homework for high achieving students!
  - (I have not tried this, but I think it's a valid way of doing this)

# AM example

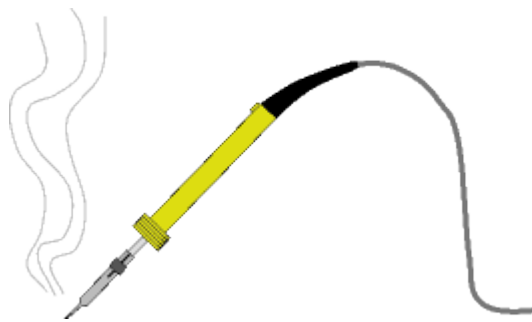
VK1SV 50 W, 160 m transmitter



# Ideas

- LF/MF transmitter of course!
- 10.140 MHz QRSS beacon (other freqs too!)
- AM transmitter for 160m/80m/40m
  - 7.125 MHz AM hobebrewer's network every Saturday morning
  - Combine with super simple single conversion superhet receiver, based on AM-radio-in-a-chip (a topic for a future presentation?)
- High power CW transmitter that fits in your pocket
  - Watch those key clicks!
- QRP CW transmitter for field/fun use!
  - Xtal oscillator
- Dedicated WSPR beacon (combine with DDS)
- Opera beacon (like WSPR only single freq – CW TX)





Questions?